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December 2013

### IRF644B

# N-Channel BFET MOSFET 250 V, 14 A, 280 m $\Omega$

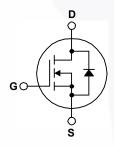
### **Description**

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

### **Features**

- 14 A, 250 V,  $R_{DS(on)}$  = 280 m $\Omega$  @  $V_{GS}$  = 10 V
- Low gate charge (Typ. 47 nC)
- · Low Crss (Typ. 30 pF)
- · Fast Switching
- · 100% Avalanche Tested
- · Improved dv/dt Capability





### **Absolute Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter		IRF644B_FP001	Unit
V <sub>DSS</sub>	Drain-Source Voltage		250	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		14	Α
	- Continuous (T <sub>C</sub> = 100°C)		8.9	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	56	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	480	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	14	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	13.9	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.8	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		139	W
	- Derate Above 25°C		1.11	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

### **Thermal Characteristics**

Symbol	Parameter	IRF644B_FP001	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.9	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
IRF644B_FP001	IRF644B	TO-220	Tube	N/A	N/A	50 units

### **Flactrical Characteristics**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	250			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.24		V/°C
I <sub>DSS</sub>	7 0 1 1/1 5 1 0 1	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V			10	μΑ
Zero Gate Voltage	Zero Gate Voltage Drain Current	$V_{DS} = 200 \text{ V}, T_{C} = 125^{\circ}\text{C}$			100	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.0 A		0.22	0.28	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 7.0 A		11.7		S
Dynam	ic Characteristics			•		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		1250	1600	pF
C <sub>oss</sub>	Output Capacitance			150	195	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			30	40	pF
Switch	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 14 A,		20	50	ns
t <sub>r</sub>	Turn-On Rise Time	$R_{G} = 25 \Omega$		115	240	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	11.6 20 32		150	310	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	95	200	ns
	Total Gate Charge	V <sub>DS</sub> = 200 V, I <sub>D</sub> = 14 A,		47	60	nC
Qg						
U	Gate-Source Charge	V <sub>GS</sub> = 10 V	/	6.2		nC
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Gate-Source Charge Gate-Drain Charge	7 20 2		6.2		
Q <sub>gs</sub> Q <sub>gd</sub>	Gate-Drain Charge	V <sub>GS</sub> = 10 V (Note 4)				
Q <sub>gs</sub> Q <sub>gd</sub> Drain-S	Gate-Drain Charge  Source Diode Characteristics and	V <sub>GS</sub> = 10 V (Note 4)		23		nC
Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-S</b>	Gate-Drain Charge  Source Diode Characteristics at  Maximum Continuous Drain-Source Dio	V <sub>GS</sub> = 10 V  (Note 4)  nd Maximum Ratings ode Forward Current		23	14	nC A
$Q_{gs}$ $Q_{gd}$ Drain-S $I_{S}$ $I_{SM}$	Gate-Drain Charge  Source Diode Characteristics at Maximum Continuous Drain-Source Diode Maximum Pulsed Drain-Source Diode F	v <sub>GS</sub> = 10 V (Note 4)  nd Maximum Ratings ode Forward Current  Forward Current			 14 56	nC A A
Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-S</b>	Gate-Drain Charge  Source Diode Characteristics at  Maximum Continuous Drain-Source Dio	V <sub>GS</sub> = 10 V  (Note 4)  nd Maximum Ratings ode Forward Current		23	14	

Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 3.9 mH,  $I_{AS}$  = 14 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega_{c}$  starting  $T_{J}$  = 25°C. 3.  $I_{SD} \leq$  14 A, di/dt  $\leq$  300 A/µs,  $V_{DD} \leq$  BV<sub>DSS</sub>, starting  $T_{J}$  = 25°C. 4. Essentially independent of operating temperature.

### **Typical Characteristics**

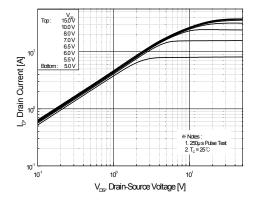


Figure 1. On-Region Characteristics

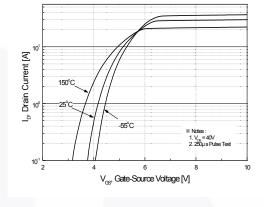


Figure 2. Transfer Characteristics

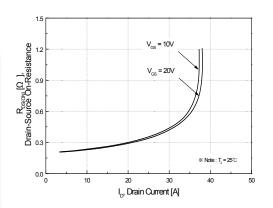


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

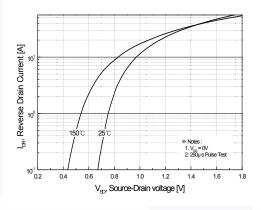


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

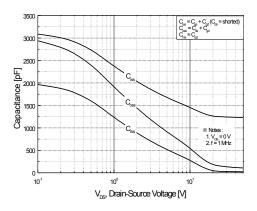


Figure 5. Capacitance Characteristics

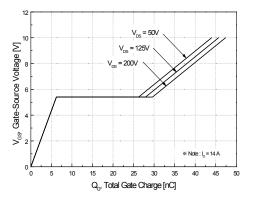
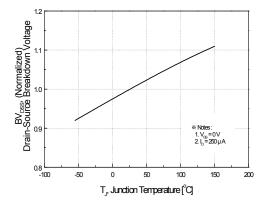


Figure 6. Gate Charge Characteristics

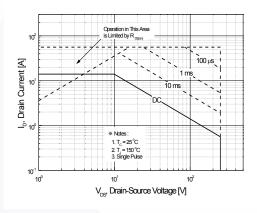
### Typical Characteristics (Continued)



3.0 2.5 (N) 2.

Figure 7. Breakdown Voltage Variation vs Temperature





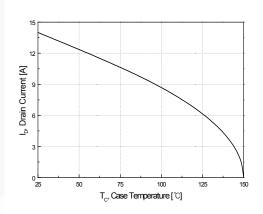


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs Case Temperature

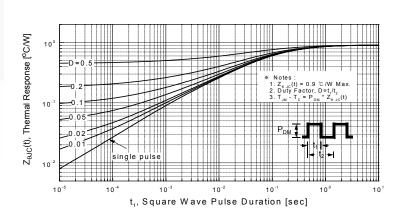


Figure 11. Transient Thermal Response Curve

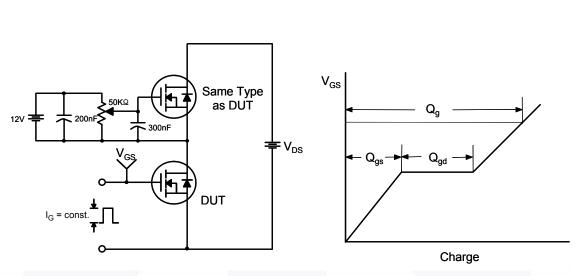


Figure 12. Gate Charge Test Circuit & Waveform

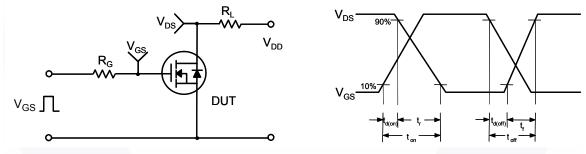


Figure 13. Resistive Switching Test Circuit & Waveforms

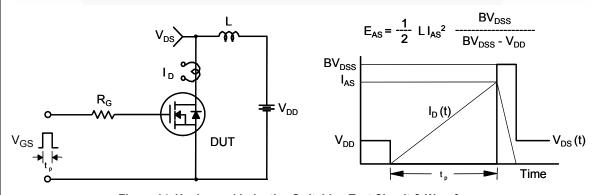
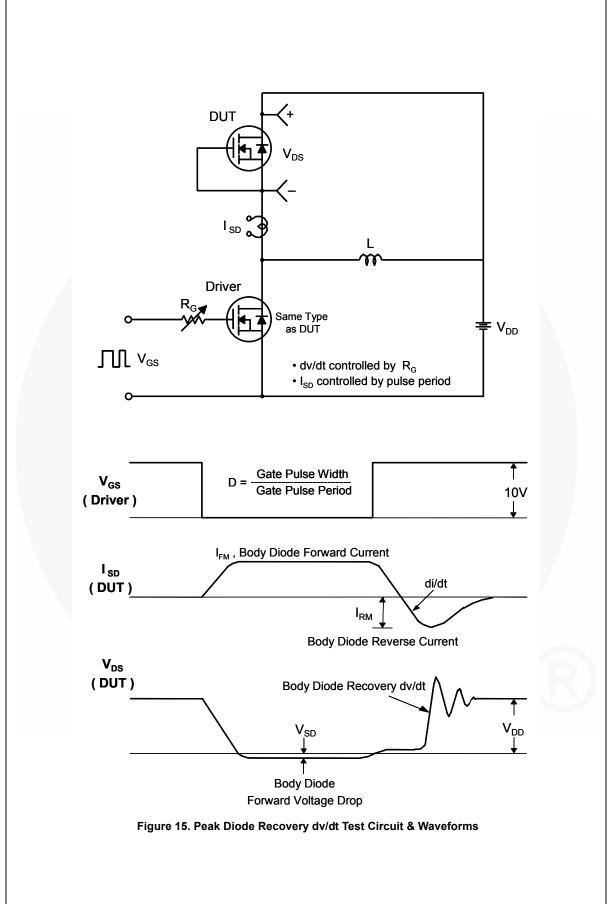


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**

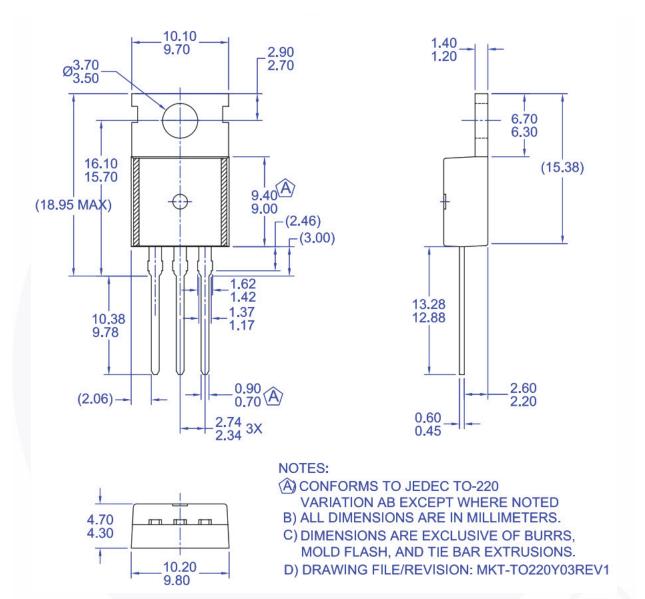


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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